

Title (en)
SEMICONDUCTOR DEVICE FABRICATION METHOD

Title (de)
VERFAHREN ZUR HERSTELLUNG EINES HALBLEITERBAUELEMENTS

Title (fr)
PROCÉDÉ DE FABRICATION DE DISPOSITIF À SEMI-CONDUCTEURS

Publication
EP 2787526 A1 20141008 (EN)

Application
EP 12853561 A 20120522

Priority
• JP 2011264285 A 20111202
• JP 2012062982 W 20120522

Abstract (en)
A method for manufacturing a MOSFET (1) includes the steps of: preparing a substrate (10) made of silicon carbide; forming a drain electrode (51) making ohmic contact with the substrate (10); and forming a backside pad electrode (80) on and in contact with the drain electrode (51). The drain electrode (51) formed in the step of forming the drain electrode (51) is made of an alloy containing Ti and Si. Further, the backside pad electrode (80) formed is maintained at a temperature of 300 °C or smaller until completion of the MOSFET (1). Accordingly, the manufacturing process can be efficient while achieving excellent adhesion between the electrodes.

IPC 8 full level
H01L 21/28 (2006.01); **H01L 21/336** (2006.01)

CPC (source: CN EP US)
H01L 21/046 (2013.01 - CN EP US); **H01L 21/0485** (2013.01 - CN EP US); **H01L 21/049** (2013.01 - CN EP US); **H01L 29/45** (2013.01 - EP US); **H01L 29/66068** (2013.01 - CN EP US); **H01L 29/7802** (2013.01 - EP US); **H01L 29/7827** (2013.01 - CN); **H01L 2924/0002** (2013.01 - CN EP US)

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